

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary)					ATTY. DOCKET NO.		SERIAL NO.	
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<b>U.S. PATENT DOCUMENTS</b>								
Examiner's Initials		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
	AA							
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	AI							
	AJ							
	AK							
	AL							
<b>FOREIGN PATENT DOCUMENTS</b>								
		Document Number	Date	Country		Class	Subclass	Translation Yes      No
	AM							
<b>OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)</b>								
<i>YF</i>	AN		ARMAS, B., et al., "Chemical Vapor Deposition Of $Si_3N_4$ and AlN on Carbon Fibers", <u>Chemical Vapor Deposition 1987</u> , The Electrochemical Society, Inc., Proceedings Vol 87-8, pp. 1060-69 (1987)					
	AO		SUZUKI, M., et al., "CVD Of Polycrystalline Aluminum Nitride", <u>Chemical Vapor Deposition 1987</u> , The Electrochemical Society, Inc., Proceedings Vol 87-8, pp. 1089-97 (1987)					
	AP		KOBAYASHI, N., et al., <u>Improved 2DEG Mobility In Selectively Doped GaAs/N-AlGaAs Grown by MOCVD Using Triethyl Organometallic Compounds</u> , Musashino Elect. Comm. Lab., Nippon Tel & Telegraph, Japan, 2 Pages, (9/10/1984)					
	AQ		PIERSON, Hugh O., <u>Handbook Of Chemical Vapor Deposition (CVD)</u> , Noyes Publications, N.J., pp. 216-219 (undated)					
	AR		<u>CVD Of Nonmetals</u> , Editor: William S. Rees, Jr., pp. 301-307 (1996)					
	AS		C. Jimenez et al., <u>Preparation of aluminum nitride films by low pressure organometallic chemical vapor deposition</u> , 78-77 SURFACE AND COATINGS TECHNOLOGY 372-378 (1995).					
<i>YF</i>	AT		H. Liu et al., <u>The surface chemistry of aluminum nitride MOCVD on alumina using trimethylaluminum and ammonia as precursors</u> , 320 SURFACE SCIENCE 145-160 (1994).					
EXAMINER				DATE CONSIDERED				
<i>Weller</i>				<i>9/24/02</i>				
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## U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
YH	AA	5,656,113	08/97	IKEDA ET AL.			
	AB	5,709,928	01/98	IKEDA ET AL.			
	AC	5,605,858	02/97	NISHIOKA ET AL.			
	AD	5,687,112	11/97	OVSHINSKY			
	AE	5,767,578	06/98	CHANG ET AL.			
	AF	5,773,882	06/98	IWASAKI			
	AG	5,783,483	07/98	GARDNER			
	AH	5,783,716	07/98	BAUM ET AL.			
	AI	5,786,635	07/98	ALCOE ET AL.			
	AJ	5,786,259	07/98	KANG			
	AL	5,183,684	02/02/93	Carpenter			
	AM	5,356,608	10/18/94	Gebhardt			
	AN	5,573,742	11/12/96	Gebhardt			
	AO	5,599,732	02/04/97	Razeghi			
	AP	5,650,361	07/22/97	Radhakrishnan			
YH	AQ	09/191,294	11/98	BRENDA D. KRAUS ET AL.			11-13-98
	AR						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
YH	AS	JP401230779A	09/14/89	Hayashi et al.				
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